

International IR Rectifier

PD - 95595

IRFIZ46NPbF

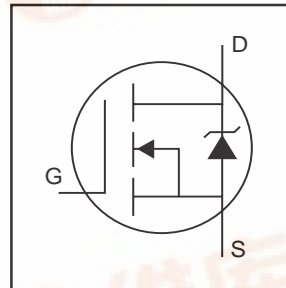
HEXFET® Power MOSFET

- Advanced Process Technology
- Isolated Package
- High Voltage Isolation = 2.5KVRMS ⑤
- Sink to Lead Creepage Dist. = 4.8mm
- Fully Avalanche Rated
- Lead-Free

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

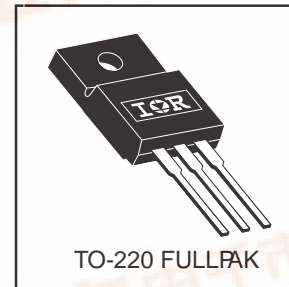
The TO-220 Fullpak eliminates the need for additional insulating hardware in commercial-industrial applications. The moulding compound used provides a high isolation capability and a low thermal resistance between the tab and external heatsink. This isolation is equivalent to using a 100 micron mica barrier with standard TO-220 product. The Fullpak is mounted to a heatsink using a single clip or by a single screw fixing.



$$V_{DS} = 55V$$

$$R_{DS(on)} = 0.020\Omega$$

$$I_D = 33A$$



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	33	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	23	
I_{DM}	Pulsed Drain Current ①⑥	180	
$P_D @ T_C = 25^\circ C$	Power Dissipation	45	W
	Linear Derating Factor	0.3	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy ②⑥	230	mJ
I_{AR}	Avalanche Current ③⑥	16	A
E_{AR}	Repetitive Avalanche Energy ④⑥	4.5	mJ
dv/dt	Peak Diode Recovery dv/dt ⑤⑥	5.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

Thermal Resistance

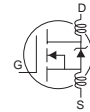
	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	---	---	3.3	°C/W
$R_{\theta JA}$	Junction-to-Ambient	---	---	65	



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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.017	—	V/°C	Reference to 25°C , $I_D = 1\text{mA}$ ⓐ
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.020	Ω	$V_{GS} = 10V, I_D = 19A$ ⓐ
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	16	—	—	S	$V_{DS} = 25V, I_D = 28A$ ⓐ
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 55V, V_{GS} = 0V$ $V_{DS} = 44V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100	nA	$V_{GS} = -20V$
Q_g	Total Gate Charge	—	—	61	nC	$I_D = 28A$
Q_{gs}	Gate-to-Source Charge	—	—	13	nC	$V_{DS} = 44V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	24	nC	$V_{GS} = 10V$, See Fig. 6 and 13 ⓐⓑ
$t_{d(on)}$	Turn-On Delay Time	—	12	—	ns	$V_{DD} = 28V$ $I_D = 28A$ $R_G = 12\Omega$ $R_D = 0.98\Omega$, See Fig. 10 ⓐⓑ
t_r	Rise Time	—	80	—		
$t_{d(off)}$	Turn-Off Delay Time	—	43	—		
t_f	Fall Time	—	52	—		
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	1500	—	pF	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1.0\text{MHz}$, See Fig. 5ⓐ
C_{oss}	Output Capacitance	—	450	—		
C_{rss}	Reverse Transfer Capacitance	—	160	—		
C	Drain to Sink Capacitance	—	12	—		



Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	33	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ⓐⓑ	—	—	180		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 19A, V_{GS} = 0V$ ⓐ
t_{rr}	Reverse Recovery Time	—	72	110	ns	$T_J = 25^\circ\text{C}, I_F = 28A$
Q_{rr}	Reverse Recovery Charge	—	210	310	nC	$di/dt = 100A/\mu s$ ⓐⓑ

Notes:

- ⓐ Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ⓑ $V_{DD} = 25V$, starting $T_J = 25^\circ\text{C}$, $L = 410\mu H$
 $R_G = 25\Omega, I_{AS} = 28A$. (See Figure 12)
- ⓒ $I_{SD} \leq 28A, di/dt \leq 240A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 175^\circ\text{C}$
- ⓓ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- ⓔ $t=60s, f=60\text{Hz}$
- ⓕ Uses IRFZ46N data and test conditions

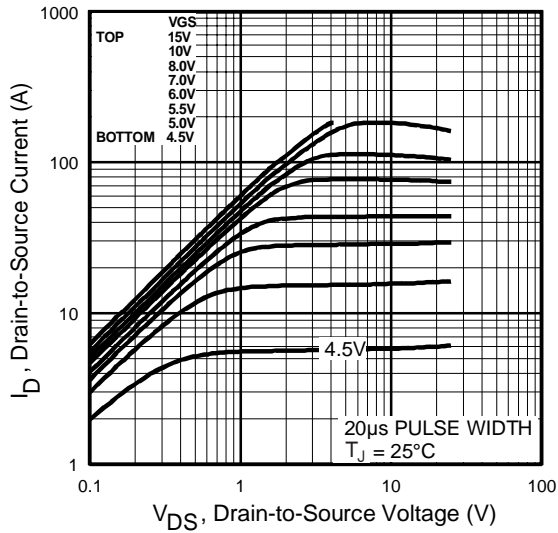


Fig 1. Typical Output Characteristics

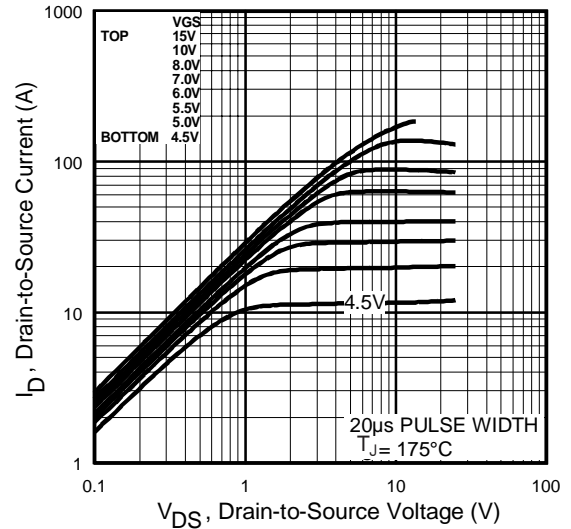


Fig 2. Typical Output Characteristics

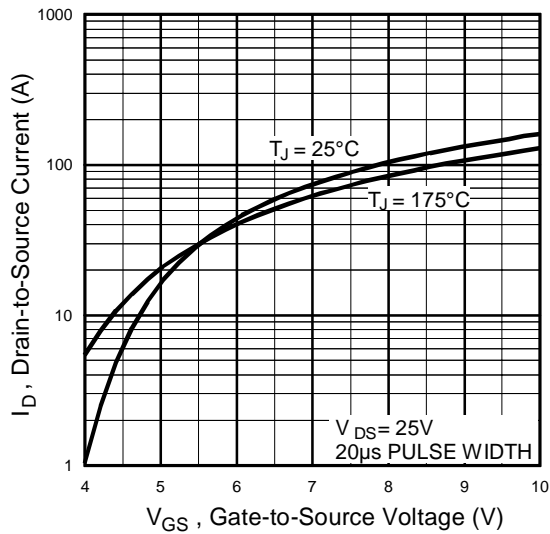


Fig 3. Typical Transfer Characteristics

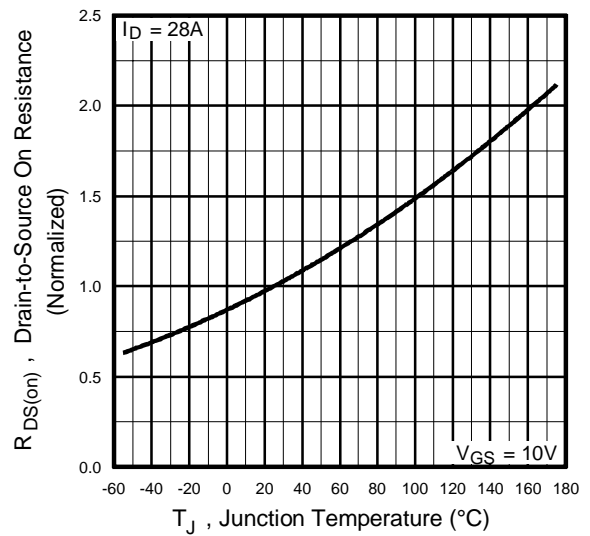


Fig 4. Normalized On-Resistance Vs. Temperature

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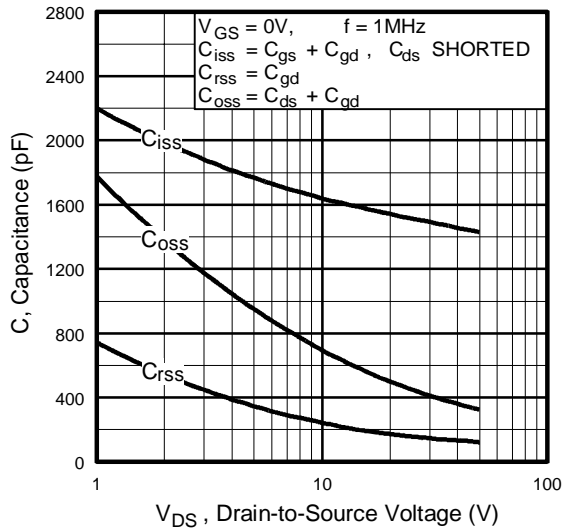


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

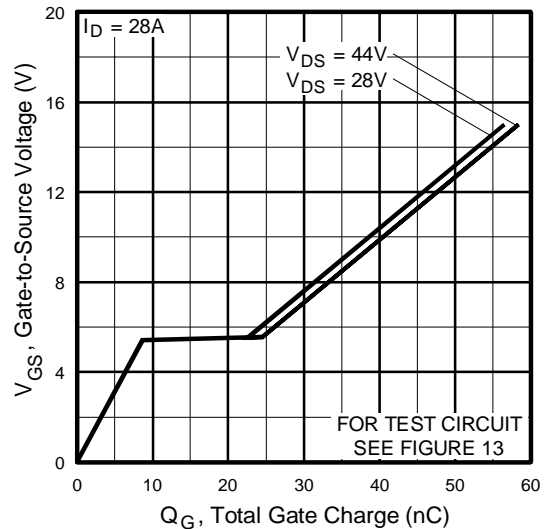


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

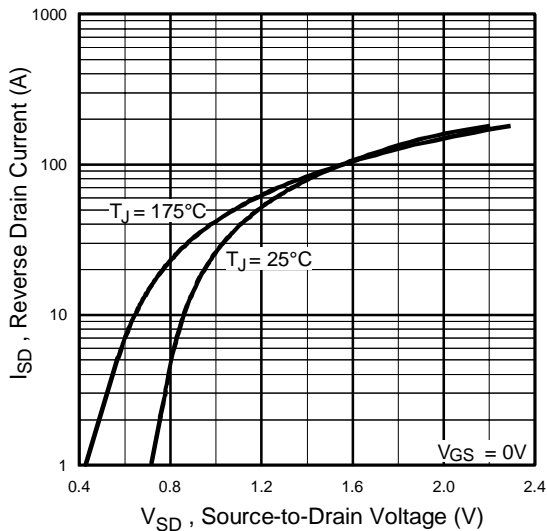


Fig 7. Typical Source-Drain Diode Forward Voltage

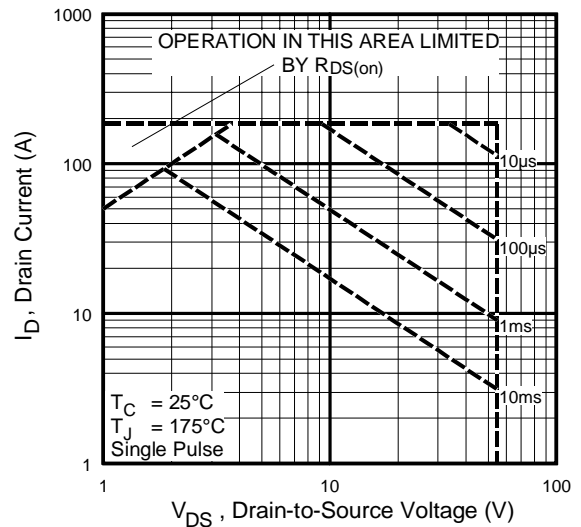


Fig 8. Maximum Safe Operating Area

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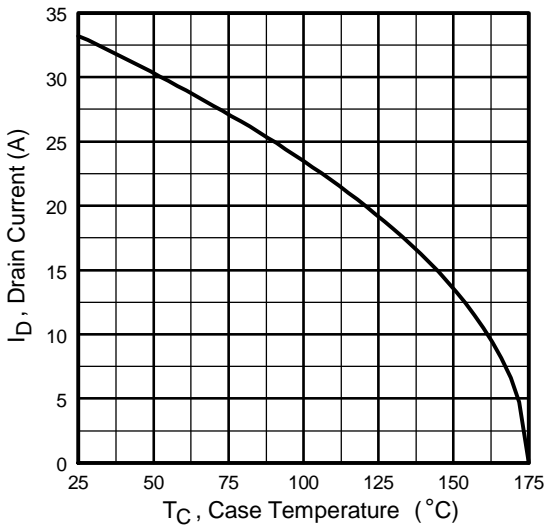


Fig 9. Maximum Drain Current Vs. Case Temperature

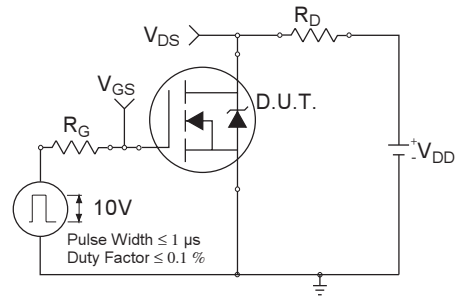


Fig 10a. Switching Time Test Circuit

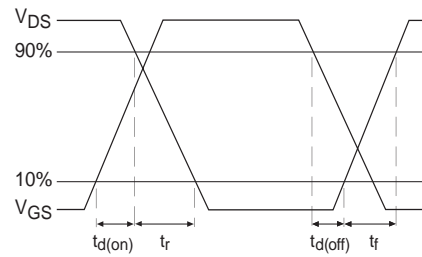


Fig 10b. Switching Time Waveforms

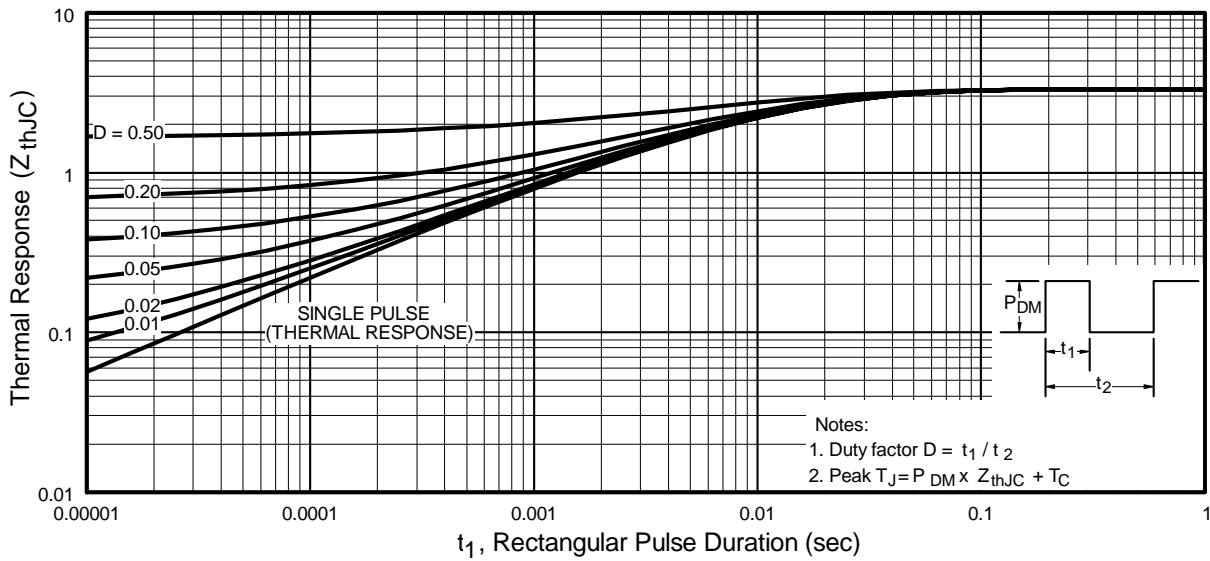


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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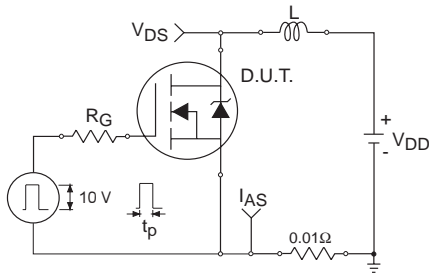


Fig 12a. Unclamped Inductive Test Circuit

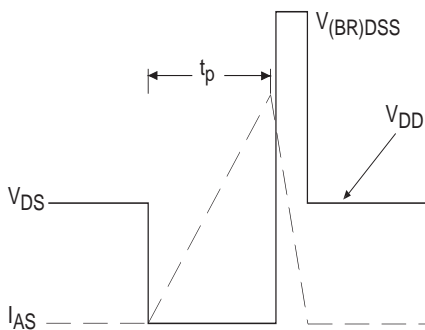


Fig 12b. Unclamped Inductive Waveforms

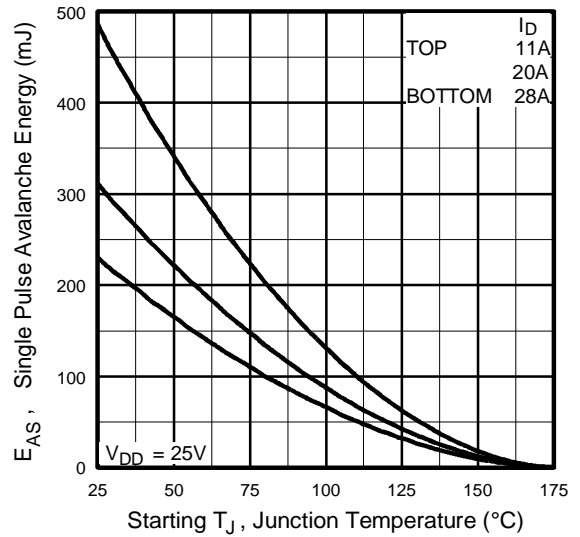


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

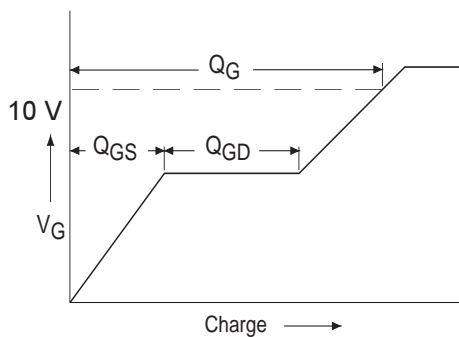


Fig 13a. Basic Gate Charge Waveform

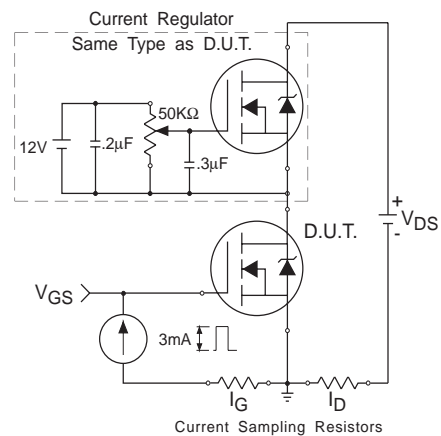
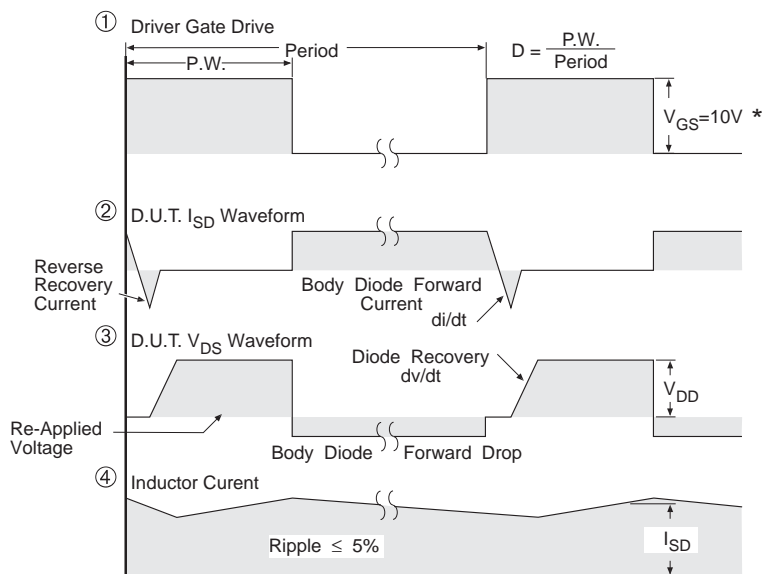
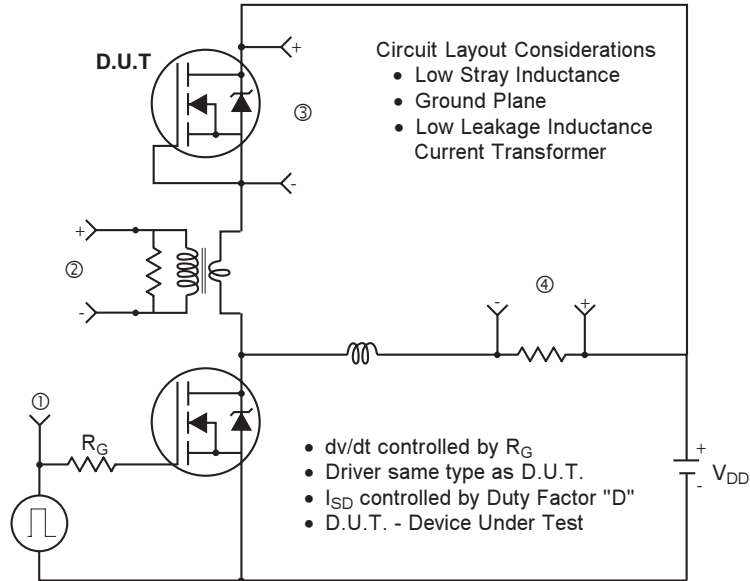


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



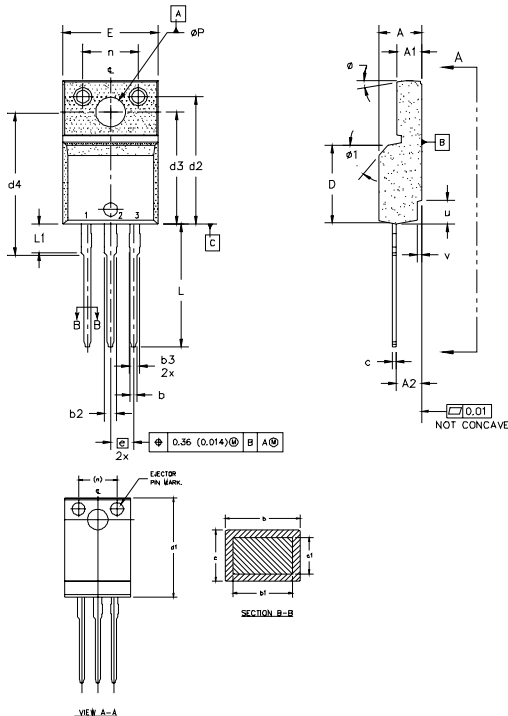
* $V_{GS} = 5V$ for Logic Level Devices

Fig 14. For N-Channel HEXFETS

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TO-220 Full-Pak Package Outline

Dimensions are shown in millimeters (inches)



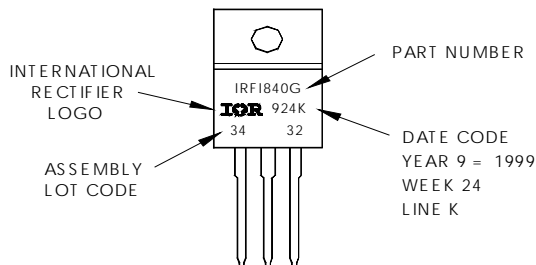
- NOTES:
- 1.0 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
 - 2.0 DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
 - 3.0 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
 - 4.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH; MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
 - 5.0 DIMENSION d1 APPLY TO BASE METAL ONLY.
 - 6.0 STEP OPTIONAL ON PLASTIC BODY DEFINED BY DIMENSIONS u & v.
 - 7.0 CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES	LEAD ASSIGNMENTS
	MILLIMETERS		INCHES			
	MIN.	MAX.	MIN.	MAX.		
A	4.57	4.83	0.180	0.190		
A1	2.57	2.83	0.101	0.114		HEXFLET
A2	2.57	2.85	0.099	0.112		
b	0.622	0.89	0.024	0.035	5	1.- GATE 2.- DRAIN 3.- SOURCE
b1	0.622	0.858	0.024	0.033		
b2	1.229	1.400	0.048	0.055		
b3	1.229	1.400	0.048	0.055		
c	0.440	0.629	0.017	0.025		
c1	0.440	0.564	0.017	0.023		
D	8.65	9.80	0.341	0.386	4	
d1	16.80	16.12	0.622	0.635		
d2	13.97	14.22	0.550	0.560		
d3	12.30	12.52	0.484	0.509		
d4	8.64	9.91	0.340	0.390		
E	10.36	10.63	0.408	0.419	4	
e	2.54 BSC		0.100 BSC			
L	13.20	13.73	0.520	0.541	3	
L1	3.10	3.50	0.122	0.138		
n	6.05	6.15	0.238	0.242		
phi P	3.05	3.45	0.120	0.136		
u	2.40	2.50	0.094	0.098	6	
v	0.40	0.50	0.016	0.020		
phi	3°	7°	3°	7°		
phi 1		45°		45°		

TO-220 Full-Pak Part Marking Information

EXAMPLE: THIS IS AN IRF1840G
WITH ASSEMBLY
LOT CODE 3432
ASSEMBLED ON WW 24 1999
IN THE ASSEMBLY LINE "K"

Note: "P" in assembly line position indicates "Lead-Free"



Data and specifications subject to change without notice.



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Visit us at www.irf.com for sales contact information. 07/04

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>